

CMSD4448

**SUPER-MINI
HIGH SPEED
SWITCHING DIODE**

**SUPERTM
mini**



SOT-323 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSD4448 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded super-mini surface mount package, designed for high speed switching applications.

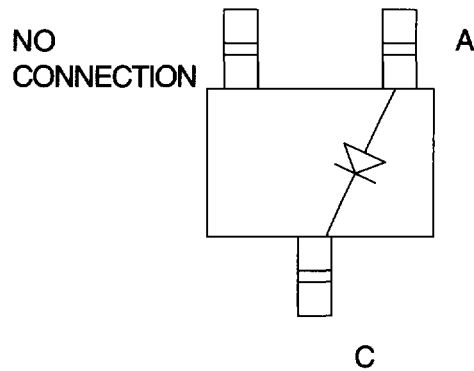
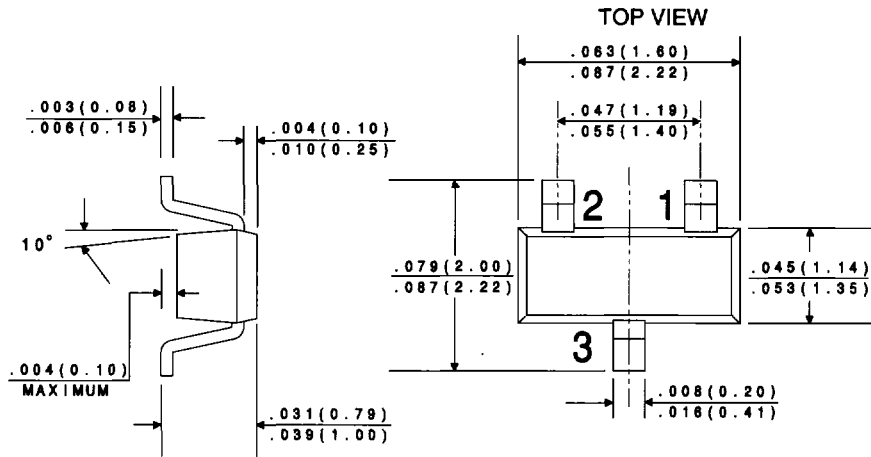
MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, $t_p=1\mu\text{sec}$.	I_{FSM}	4000	mA
Forward Surge Current, $t_p=1\text{ sec}$.	I_{FSM}	1000	mA
Power Dissipation	P_D	250	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	500	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_{BR}	$I_R=5.0\mu\text{A}$	75		V
V_{BR}	$I_R=100\mu\text{A}$	100		V
I_R	$V_R=20\text{V}$		25	nA
V_F	$I_F=5.0\text{mA}$	0.62	0.72	V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1\text{ MHz}$		4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		4.0	ns

All dimensions in inches (mm).



DATA
SHEET

R1